



## Description

The HIPD50N06S4L08ATMA2 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L  
(TO-252)

## General Features

$V_{DS} = 60V$   $I_D = 80A$

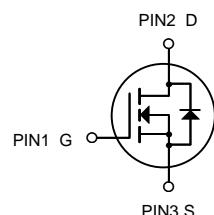
$R_{DS(ON)} < 8m\Omega$  @  $V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HIPD50N06S4L08ATMA2	TO-252-2L(TO-252)	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	43	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	272	A
$I_{AS}$	Avalanche Current	28	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation <sup>4</sup>	104	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62.5	°C/W



**Electrical Characteristics@Tj=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
R <sub>DSON</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =45A	-	6	8	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A	-	8.3	15	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.4	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =30A	-	71	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	10	uA
	Drain-Source Leakage Current (T <sub>j</sub> =125°C)	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	250	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =30A V <sub>DS</sub> =48V V <sub>GS</sub> =4.5V	-	33	45	nC
Q <sub>gs</sub>	Gate-Source Charge		-	5	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge		-	21	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =30V I <sub>D</sub> =30A R <sub>G</sub> =3.3Ω V <sub>GS</sub> =10V	-	10	-	ns
t <sub>r</sub>	Rise Time		-	43	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	47	-	ns
t <sub>f</sub>	Fall Time		-	80	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V V <sub>DS</sub> =25V f=1.0MHz	-	2680	3300	pF
C <sub>oss</sub>	Output Capacitance		-	260	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	180	-	pF
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =45A, V <sub>GS</sub> =0V	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =10A, V <sub>GS</sub> =0V, dI/dt=100A/μs	-	30	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	18	-	nC



### Typical Performance Characteristics

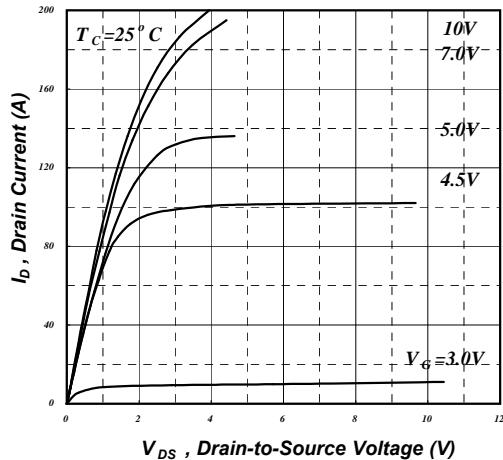


Fig 1. Typical Output Characteristics

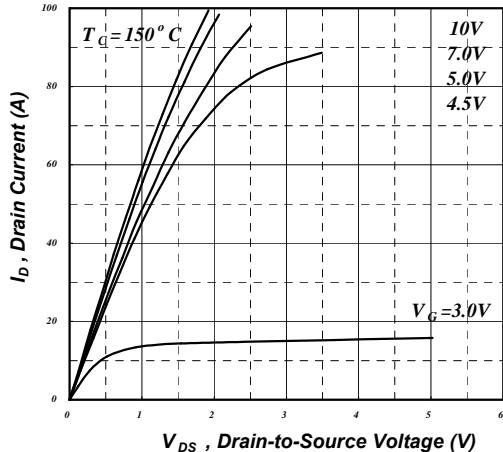


Fig 2. Typical Output Characteristics

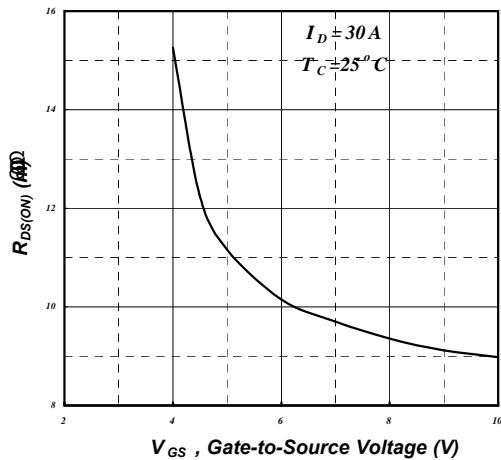


Fig 3. On-Resistance v.s. Gate Voltage

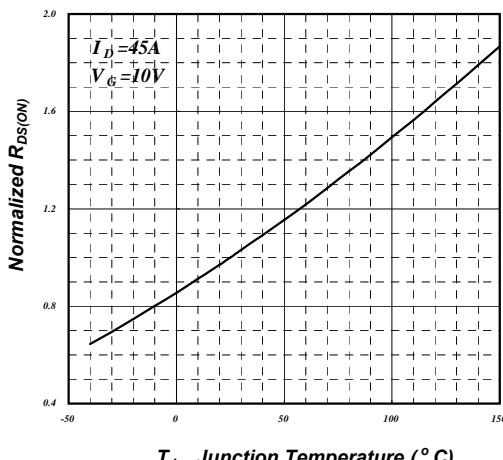


Fig 4. Normalized On-Resistance v.s. Junction Temperature

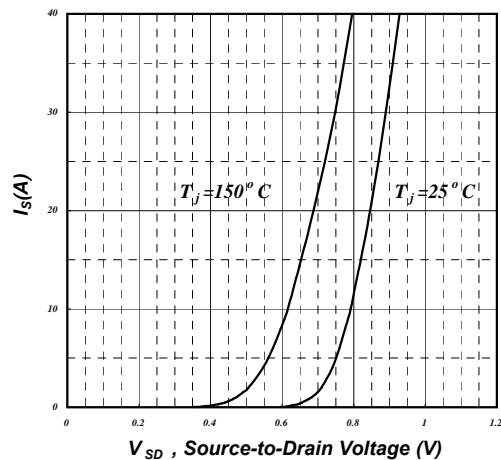


Fig 5. Forward Characteristic of Reverse Diode

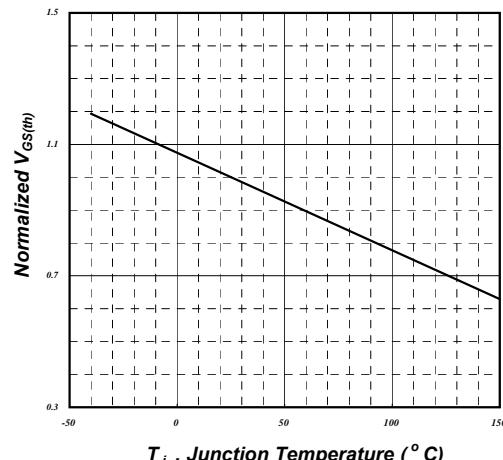


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

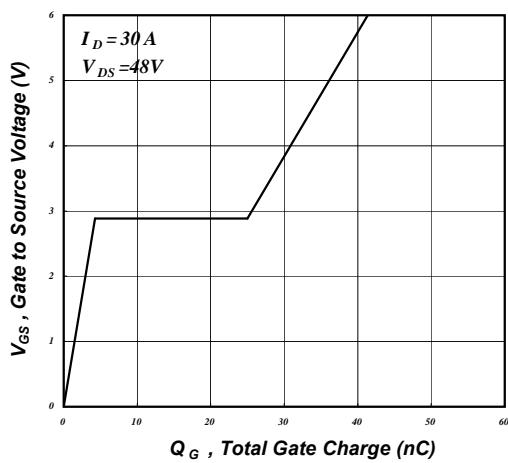


Fig 7. Gate Charge Characteristics

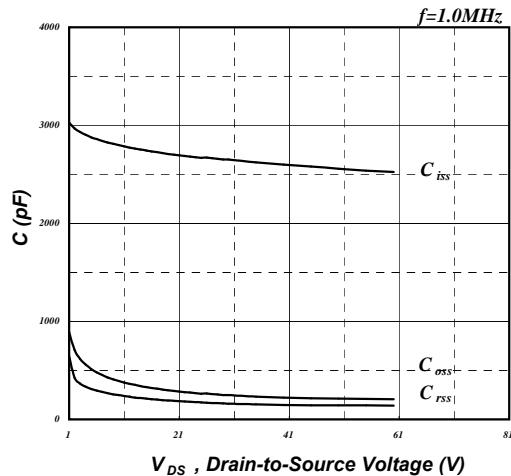


Fig 8. Typical Capacitance Characteristics

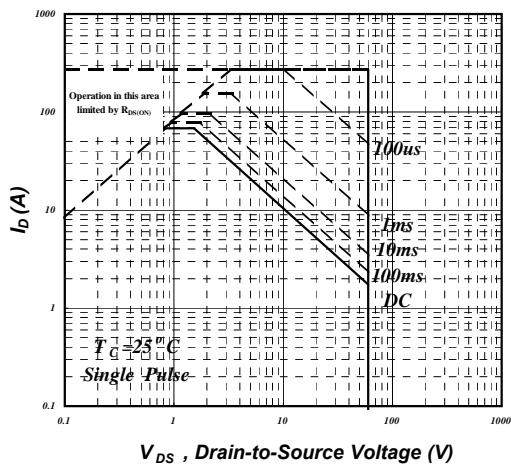


Fig 9. Maximum Safe Operating Area

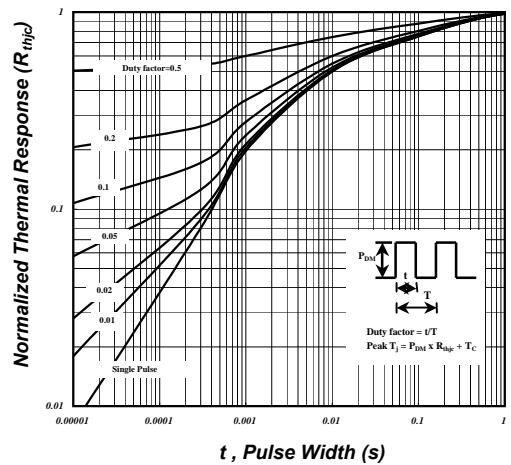


Fig 10. Effective Transient Thermal Impedance

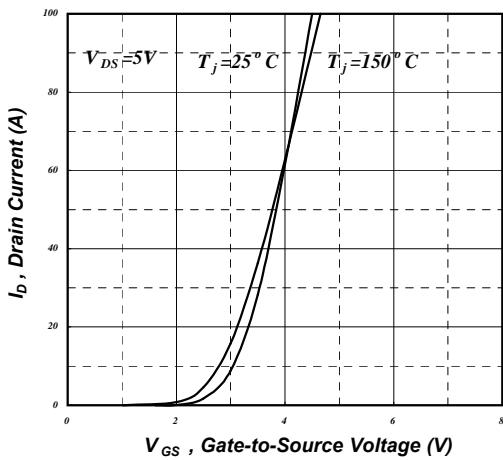


Fig 11. Transfer Characteristics

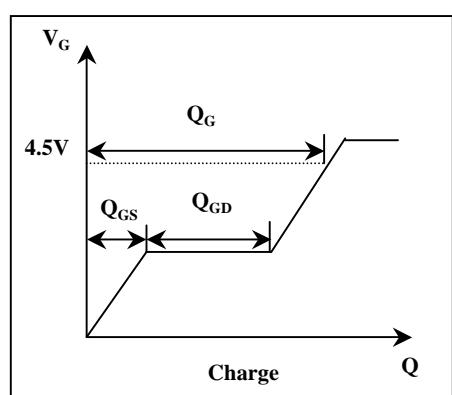
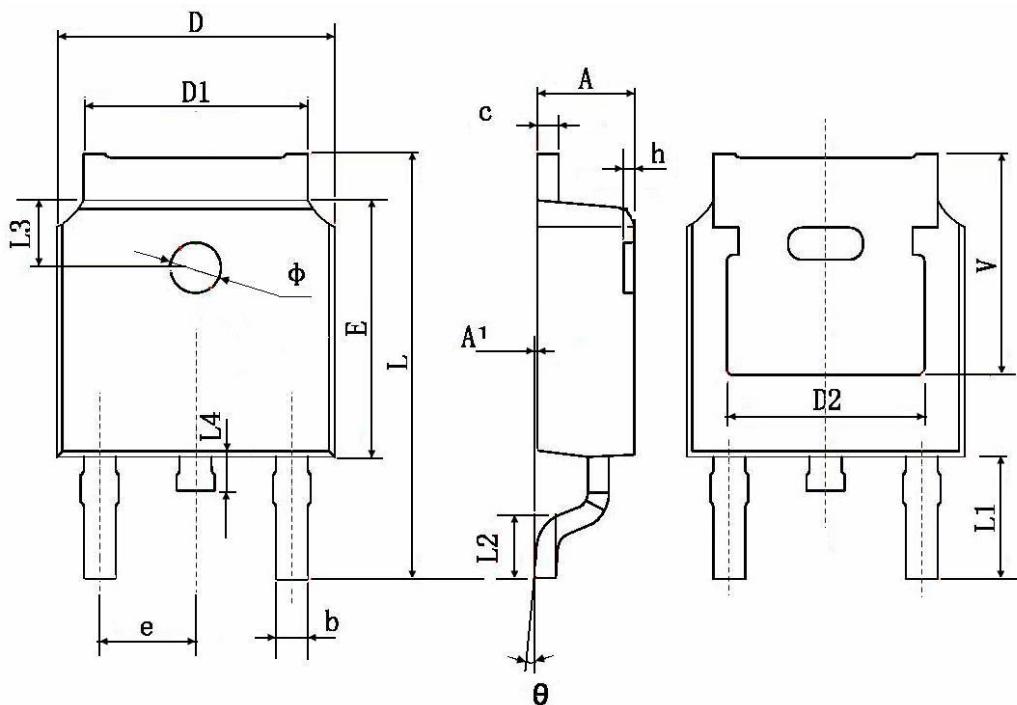


Fig 12. Gate Charge Waveform



TO252-2L(TO-252) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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